

Vishay Siliconix

Low-Voltage Single SPDT Analog Switch

DESCRIPTION

The DG2002 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 8 ns, t_{OFF} : 6 ns), low on-resistance ($r_{DS(on)}$: 7 Ω) and small physical size (SC70), the DG2002 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG2002 is built on Vishay Siliconix's low voltage JI2 process. An epitaxial layer prevents latchup. Break-before - make is guaranteed for DG2002.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

FEATURES

- Low voltage operation (1.8 V to 5.5 V)
- Low on-resistance $r_{DS(on)}$: 7 Ω
- Fast switching t_{ON} : 8 ns, t_{OFF}: 6 ns
- Low charge injection Q_{INJ}: 5 pC
- Low power consumption
- TTL/CMOS compatible
- 6-pin SC70 package

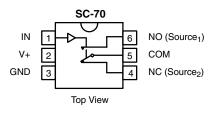
BENEFITS

- Reduced power consumption
- Simple logic interface
- High accuracy
- Reduce board space

APPLICATIONS

- Cellular phones
- Communication systems
- Portable test equipment
- · Battery operated systems
- Sample and hold circuits

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device Marking: E2xx

TRUTH TABLE						
Logic	NC	NO				
0	ON	OFF				
1	OFF	ON				

ORDERING INFORMATION						
Temp Range	Package	Part Number				
- 40 to 85 °C	SC70-6	DG2002DL-T1 DG2002DL-T1-E3				

* Pb containing terminations are not RoHS compliant, exemptions may apply.



RoHS

COMPLIANT

Vishay Siliconix



ABSOLUTE MAXIMUM RATINGS							
Parameter		Limit	Unit				
Referenced V+ to GND		- 0.3 to +6	V				
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	7 °				
Continuous Current (Any Terminal)		± 50	mA				
Peak Current (Pulsed at 1 ms, 10 % of	luty cycle)	± 200	IIIA				
Storage Temperature		- 65 to + 150	°C				
Power Dissipation (Packages) ^b	6-Pin SC70 ^c	250	mW				

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
b. All leads welded or soldered to PC Board.
c. Derate 3.1 mW/°C above 70 °C.

SPECIFICATIONS V-		Test Conditions Unless Otherwise Specified	1	Limits - 40 to 85 °C			
		V+ = 2.0 V, ± 10 %		_			-
Parameter	Symbol	V _{IN} = 0.4 or 1.6 V ^e	Temp ^a	Min ^b	Тур ^с	Max ^b	Unit
Analog Switch			T	1	1	1	1
Analog Signal Range ^d	V _{NO} , V _{NC} V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}	$V_{+} = 1.8 V, V_{COM} = 1.0 V, I_{NO}, I_{NC} = 10 mA$			38 39.3	46.1 47.1	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	$V_{+} = 1.8 V, V_{COM} = 0 \text{ to } V_{+}, I_{NO}, I_{NC} = 10 \text{ mA}$			21		52
	I _{NO(off)} I _{NC(off)}	off) $V + = 2.2 V$		- 250 - 3.0		250 3.0	pA nA
Switch Off Leakage Current ^t	I _{COM(off)}	V_{NO} , $V_{NC} = 0.5 \text{ V}/1.5 \text{ V}$, $V_{COM} = 1.5 \text{ V}/0.5 \text{ V}$	Room Full ^d	- 250 - 3.0		250 3.0	pA nA
Channel-On Leakage Current ^f	I _{COM(on)}	V+ = 2.2 V, V _{NO} , V _{NC} = V _{COM} = 0.5 V/1.5 V	Room Full ^d	- 250 - 3.0		250 3.0	pA nA
Digital Control							
Input High Voltage	V _{INH}		Full			v	
Input Low Voltage	V _{INL}		Full			0.4	v
Input Capacitance ^d	C _{in}		Full		3		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}		Room Full ^d		22	31 32	
Turn-Off Time	t _{OFF}	$V_{NO} \text{ or } V_{NC}$ = 1.5 V, R_L = 300 $\Omega, \ C_L$ = 35 pF Figures 1 and 2	Room Full ^d		10	17 18	ns
Break-Before-Make Time	t _d		Room	1	12		
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω , Figure 3	Room		5	10	рС
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega_2 C_1 = 5 pF_2 f = 1 MHz$	Room		- 67		٩D
Crosstalk ^d	X _{TALK}	11 = 30.32, $0 = 3.6$ µ, $1 = 1.10$ m	Room		- 71		dB
NO, NC Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		5		pF
Channel-On Capacitance ^d	C _{ON}	Room			29		
Power Supply	н				•		
Power Supply Range	V+			1.8		2.2	V
Power Supply Current ^d	l+	V _{IN} = 0 or V+			0.01	1.0	μA
Power Consumption P _C		VIN = 0 01 V+				2.2	μW



		Test Conditions Unless Otherwise Specified V+ = 3 V, ±10 %		Limits - 40 to 85 °C			
Parameter	Symbol	$V_{\rm H} = 3 V, \pm 10 \%$ $V_{\rm IN} = 0.4 \text{ or } 2.0 \text{ V}^{\rm e}$	Temp ^a	Min ^b	Тур ^с	Max ^b	Unit
Analog Switch	-						
Analog Signal Range ^d	V _{NO} , V _{NC} V _{COM}		Full	0		V+	v
On-Resistance ^d	r _{ON}	V+ = 2.7 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 10 mA	Room Full		12.2 13	14.8 15.8	
r _{ON} Flatness ^d	r _{ON} Flatness	V+ = 2.7 V, V _{COM} = 0 to V+, I _{NO} , I _{NC} = 10 mA	Room		5		Ω
Switch Off Leakage Current ^f	I _{NO(off)} I _{NC(off)}	V+ = 3.3 V	Room Full	- 500 - 4.0		500 4.0	pA nA
Switch On Leakage Current	I _{COM(off)}	V_{NO} , V_{NC} = 1 V/3 V, V_{COM} = 3 V/1 V	Room Full	- 500 - 4.0		500 4.0	pA nA
Channel-On Leakage Current ^f	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 1 V/3 V	Room Full	- 500 - 4.0		500 4.0	pA nA
Digital Control			1		1		
Input High Voltage	V _{INH}		Full	2			v
Input Low Voltage	V _{INL}		Full			0.4	
Input Capacitance ^d	C _{in}		Full		3		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics					1	L	<u> </u>
Turn-On Time ^d	t _{ON}		Room Full		12	21 22	
Turn-Off Time ^d	t _{OFF}	$V_{NO} \text{ or } V_{NC}$ = 2.0 V, R_L = 300 $\Omega, \ C_L$ = 35 pF Figures 1 and 2	Room Full		7	14 15	ns
Break-Before-Make Time ^d	t _d		Room	1	6		
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω , Figure 3	Room		5	10	pC
Off-Isolation ^d	OIRR		Room		- 67		
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 69		dB
NO, NC Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		5		pF
Channel-On Capacitance ^d	C _{ON}		Room		29		1
Power Supply	1 1				1	1	
Power Supply Range	V+			2.7		3.3	V
Power Supply Current	l+	V _{IN} = 0 or V+			0.01	1.0	μA
Power Consumption	P _C	V _{IN} = 0 01 V+				3.3	μW

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SPECIFICATIONS V+	- = 5.0 V						
		Test Conditions Unless Otherwise Specified V+ = 5 V, ± 10 %		Limits - 40 to 85 °C			-
Parameter	Symbol	$V_{\rm IN} = 0.8 \text{ or } 2.4 \text{ V}^{\rm e}$		Min ^b	Тур ^с	Max ^b	Unit
Analog Switch			- I				
Analog Signal Range ^d	V _{NO} , V _{NC,} V _{COM}		Full	0		V+	v
On-Resistance	r _{ON}	V+ = 4.5 V, V _{COM} = 3 V, I _{NO} , I _{NC} = 10 mA	Room Full		6.4 7.4	7.8 8.8	
r _{ON} Flatness ^d	r _{ON} Flatness	V+ = 4.5 V, V _{COM} = 0 to V+, I _{NO} , I _{NC} = 10 mA	Room		3		Ω
Switch Off Leakage Current	I _{NO(off),} I _{NC(off)}	V+ = 5.5 V	Room Full	- 1.0 - 4.0		1.0 4.0	
Switch On Leakage Gulleni	I _{COM(off)}	V_{NO} , V_{NC} = 1 V/4.5 V, V_{COM} = 4.5 V/1 V	Room Full	- 1.0 - 4.0		1.0 4.0	nA
Channel-On Leakage Current	I _{COM(on)}	V+ = 5.5 V, V+ = 5.5 V V _{NO} , V _{NC} = V _{COM} = 1 V/4.5 V	Room Full	- 1.0 - 4.0		1.0 4.0	
Digital Control				1	•	1	
Input High Voltage	V _{INH}		Full	2.4			
Input Low Voltage	V _{INL}		Full			0.8	V
Input Capacitance	C _{in}		Full		3		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics				1	•	1	
Turn-On Time ^d	t _{ON}		Room Full		8	15 16	
Turn-Off Time ^d	t _{OFF}	$V_{NO} \text{ or } V_{NC}$ = 3 V, R_L = 300 Ω , C_L = 35 pF Figures 1 and 2	Room Full		6	13 14	ns
Break-Before-Make Time ^d	t _d		Room	1	4		
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω , Figure 3	Room		5	10	рС
Off-Isolation ^d	OIRR		Room		- 69		
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 69		dB
Source-Off Capacitance ^d	C _{NO(off),} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		5		pF
Channel-On Capacitance ^d	C _{ON}	R			29		
Power Supply							
Power Supply Range	V+			4.5		5.5	V
Power Supply Current	l+	$V_{IN} = 0 \text{ or } V+$			0.01	1.0	μA
Power Consumption	P _C	VIN - 0 01 VT				5.5	μW

Notes:

a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.

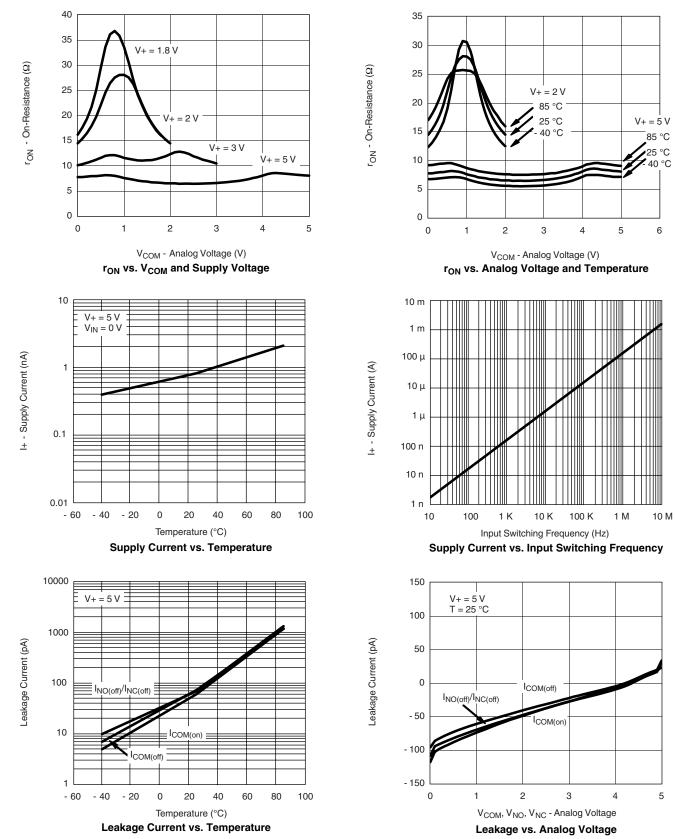
f. Guaranteed by 5 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



DG2002 Vishay Siliconix

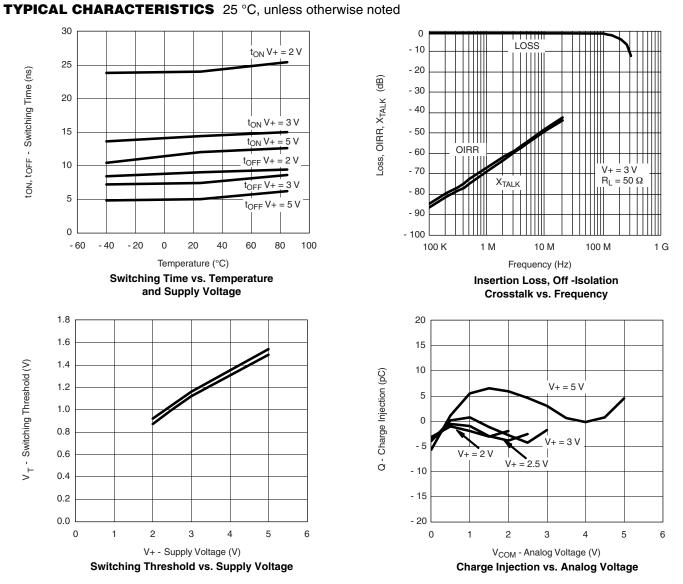
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



DG2002

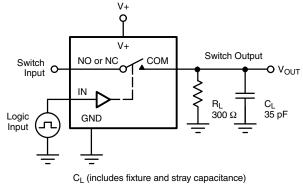
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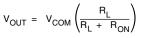


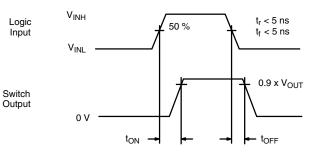


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TEST CIRCUITS

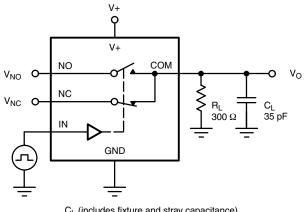


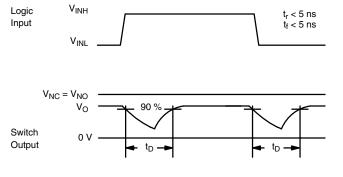




Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

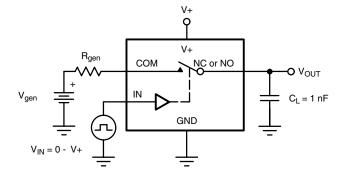


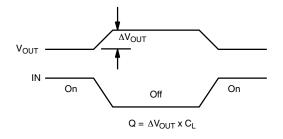




C_L (includes fixture and stray capacitance)







IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection



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TEST CIRCUITS

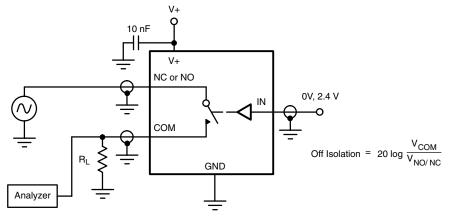


Figure 4. Off-Isolation

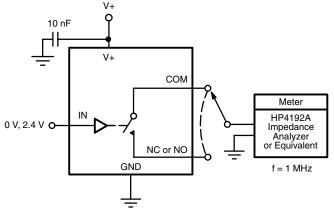


Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?71448.



Package Information Vishay Siliconix

SC-70: 6-LEADS





	MIL	LIMET	ERS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.90	-	1.10	0.035	-	0.043	
A ₁	-	-	0.10	-	-	0.004	
A ₂	0.80	-	1.00	0.031	-	0.039	
b	0.15	-	0.30	0.006	-	0.012	
С	0.10	-	0.25	0.004	-	0.010	
D	1.80	2.00	2.20	0.071	0.079	0.087	
Е	1.80	2.10	2.40	0.071	0.083	0.094	
E ₁	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65BSC			0.026BSC	;	
e ₁	1.20	1.30	1.40	0.047	0.051	0.055	
L	0.10	0.20	0.30	0.004	0.008	0.012	
٩	7°Nom 7°Nom						
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5550							



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